

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	11930	("gate electrode" or transistor) same ((oxide or "SiO.sub.2") with (dop\$3 or implant\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 13:12			
2	BRS	L2	23250	("gate electrode" or transistor) same ((oxide or "SiO.sub.2") with (dop\$3 or implant\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 13:15			
3	BRS	L3	12150	2 and @pd<="20000320"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 13:16			
4	BRS	L4	3359	((sidewall) same ("gate electrode" or transistor)) same ((oxide or "SiO.sub.2") with (dop\$3 or implant\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 13:19			
5	BRS	L5	1578	4 and @pd<="20000320"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 13:19			
6	BRS	L6	420	((sidewall) same ("gate electrode" or transistor)) same ((oxide or "SiO.sub.2") adj3 (dop\$3 or implant\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 13:20			
7	BRS	L7	208	6 and @pd<="20000320"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 13:22			
8	BRS	L8	20330	((oxide or "SiO.sub.2") adj3 (dop\$3 or implant\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 14:08			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
9	BRS	L9	13622	((oxide or "SiO.sub.2") adj2 (dop\$3 or implant\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 13:29			
10	BRS	L10	6514	((oxide or "SiO.sub.2") adj (dop\$3 or implant\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 13:21			
11	BRS	L11	187	((sidewall) same ("gate electrode" or transistor)) same 9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 13:22			
12	BRS	L12	90	11 and @pd<="20000320"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 13:30			
13	BRS	L13	4926	9 and (transistor or FET or "gate electrode")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 14:09			
14	BRS	L14	2144	13 and @pd<="20000320"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 14:09			
15	BRS	L15	3044	((oxide or "SiO.sub.2") adj3 (doping or implanting))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 14:10			
16	BRS	L16	1721	15 and (transistor or FET or "gate electrode")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 16:46			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
17	BRS	L17	911	16 and @pd<="20000320"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 14:11			
18	BRS	L18	1791	((oxide or "SiO.sub.2") adj2 (doping or implanting))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 16:36			
19	BRS	L19	920	18 and (transistor or FET or "gate electrode")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 14:11			
20	BRS	L20	505	19 and @pd<="20000320"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 16:47			
21	BRS	L21	420	(deposit\$3 or form\$3) with (oxide or "SiO.sub.2") with (non adj (uniform\$2 or conform))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 16:37			
22	BRS	L22	166	21 and (transistor or FET or "gate electrode")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 16:46			
23	BRS	L23	37	22 and @pd<="20000320"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/30 16:47			